

Table 1. Demographic characteristics of the study population	
Age (years)	Mean (SD)
18-24	20.5 (2.5)
25-34	29.5 (4.5)
35-44	39.5 (5.5)
45-54	49.5 (6.5)
55-64	59.5 (7.5)
65-74	69.5 (8.5)
75-84	79.5 (9.5)
85-94	89.5 (10.5)
95-104	99.5 (11.5)
105-114	109.5 (12.5)
115-124	119.5 (13.5)
125-134	129.5 (14.5)
135-144	139.5 (15.5)
145-154	149.5 (16.5)
155-164	159.5 (17.5)
165-174	169.5 (18.5)
175-184	179.5 (19.5)
185-194	189.5 (20.5)
195-204	199.5 (21.5)
205-214	209.5 (22.5)
215-224	219.5 (23.5)
225-234	229.5 (24.5)
235-244	239.5 (25.5)
245-254	249.5 (26.5)
255-264	259.5 (27.5)
265-274	269.5 (28.5)
275-284	279.5 (29.5)
285-294	289.5 (30.5)
295-304	299.5 (31.5)
305-314	309.5 (32.5)
315-324	319.5 (33.5)
325-334	329.5 (34.5)
335-344	339.5 (35.5)
345-354	349.5 (36.5)
355-364	359.5 (37.5)
365-374	369.5 (38.5)
375-384	379.5 (39.5)
385-394	389.5 (40.5)
395-404	399.5 (41.5)
405-414	409.5 (42.5)
415-424	419.5 (43.5)
425-434	429.5 (44.5)
435-444	439.5 (45.5)
445-454	449.5 (46.5)
455-464	459.5 (47.5)
465-474	469.5 (48.5)
475-484	479.5 (49.5)
485-494	489.5 (50.5)
495-504	499.5 (51.5)
505-514	509.5 (52.5)
515-524	519.5 (53.5)
525-534	529.5 (54.5)
535-544	539.5 (55.5)
545-554	549.5 (56.5)
555-564	559.5 (57.5)
565-574	569.5 (58.5)
575-584	579.5 (59.5)
585-594	589.5 (60.5)
595-604	599.5 (61.5)
605-614	609.5 (62.5)
615-624	619.5 (63.5)
625-634	629.5 (64.5)
635-644	639.5 (65.5)
645-654	649.5 (66.5)
655-664	659.5 (67.5)
665-674	669.5 (68.5)
675-684	679.5 (69.5)
685-694	689.5 (70.5)
695-704	699.5 (71.5)
705-714	709.5 (72.5)
715-724	719.5 (73.5)
725-734	729.5 (74.5)
735-744	739.5 (75.5)
745-754	749.5 (76.5)
755-764	759.5 (77.5)
765-774	769.5 (78.5)
775-784	779.5 (79.5)
785-794	789.5 (80.5)
795-804	799.5 (81.5)
805-814	809.5 (82.5)
815-824	819.5 (83.5)
825-834	829.5 (84.5)
835-844	839.5 (85.5)
845-854	849.5 (86.5)
855-864	859.5 (87.5)
865-874	869.5 (88.5)
875-884	879.5 (89.5)
885-894	889.5 (90.5)
895-904	899.5 (91.5)
905-914	909.5 (92.5)
915-924	919.5 (93.5)
925-934	929.5 (94.5)
935-944	939.5 (95.5)
945-954	949.5 (96.5)
955-964	959.5 (97.5)
965-974	969.5 (98.5)
975-984	979.5 (99.5)
985-994	989.5 (100.5)
995-1004	999.5 (101.5)
1005-1014	1009.5 (102.5)
1015-1024	1019.5 (103.5)
1025-1034	1029.5 (104.5)
1035-1044	1039.5 (105.5)
1045-1054	1049.5 (106.5)
1055-1064	1059.5 (107.5)
1065-1074	1069.5 (108.5)
1075-1084	1079.5 (109.5)
1085-1094	1089.5 (110.5)
1095-1104	1099.5 (111.5)
1105-1114	1109.5 (112.5)
1115-1124	1119.5 (113.5)
1125-1134	

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Commissioner for Patents  
Washington, D.C. 20231

## PRELIMINARY AMENDMENT

Sir:

Prior to calculation of the filing fee and examination,  
please amend the above-identified application as follows:

## IN THE CLAIMS

Please amend the claims as follows:

3. A method as claimed in claim 1, characterized in that use is made of gratings for the substrate overlay mark, and the resist overlay mark and the reference mark.
4. A method as claimed in claim 1, characterized in that the resist overlay mark is a latent mark.
5. A method as claimed in claim 1, characterized in that an on-axis alignment measuring device is used and in that the reference mark is a mask alignment mark.

7. A method as claimed in claim 1, characterized in that an off-axis alignment device is used.

8. A method of manufacturing devices in at least one layer of substrates, which method comprises at least one set of the following successive steps:

- aligning a mask provided with at least one overlay mark with respect to a first substrate;
- imaging, by means of projection radiation, the overlay mark in a resist layer on the substrate;
- determining the overlay between the overlay mark formed in the resist layer and an overlay mark in the substrate and correcting overlay errors;
- imaging, by means of projection radiation, a mask pattern comprising pattern features corresponding to device features to be configured in said layer in a resist layer on each substrate wherein the device features are to be formed, and
- removing material from, or adding material to, areas of said layer, which areas are delineated by the mask pattern image, characterized in that the overlay is determined by means of the method as claimed in claim 1.

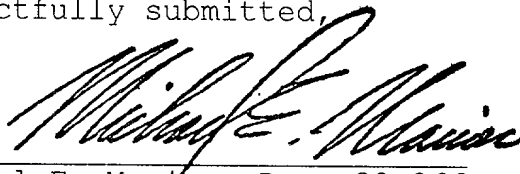
#### REMARKS

The foregoing amendments to claims 3-5 and 7-8 were made solely to avoid filing the claims in the multiple dependent form so as to avoid the additional filing fee.

The claims were not amended in order to address issues of patentability and Applicant respectfully reserves all rights he may have under the Doctrine of Equivalents. Applicant furthermore reserves his right to reintroduce

subject matter deleted herein at a later time during the  
prosecution of this application or continuing applications.

Respectfully submitted,

A handwritten signature in black ink, appearing to read "Michael E. Marion". The signature is written in a cursive, flowing style.

By  
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0940318-082601

## APPENDIX

3. A method as claimed in claim 1 ~~or 2~~, characterized in that use is made of gratings for the substrate overlay mark, and the resist overlay mark and the reference mark.

4. A method as claimed in claim 1, ~~2, or 3~~, characterized in that the resist overlay mark is a latent mark.

5. A method as claimed in claim 1, ~~2, 3 or 4~~, characterized in that an on-axis alignment measuring device is used and in that the reference mark is a mask alignment mark.

7. A method as claimed in claim 1, ~~2, 3 or 4~~, characterized in that an off-axis alignment device is used.

8. A method of manufacturing devices in at least one layer of substrates, which method comprises at least one set of the following successive steps:

- aligning a mask provided with at least one overlay mark with respect to a first substrate;
- imaging, by means of projection radiation, the overlay mark in a resist layer on the substrate;
- determining the overlay between the overlay mark formed in the resist layer and an overlay mark in the substrate and correcting overlay errors;
- imaging, by means of projection radiation, a mask pattern comprising pattern features corresponding to device features to be configured in said layer in a resist layer on each substrate wherein the device features are to be formed, and

- removing material from, or adding material to, areas of said layer, which areas are delineated by the mask pattern image, characterized in that the overlay is determined by means of the method as claimed in claim 1 ~~any one claims 1 to 7.~~

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